

UNIT

V

mΩ

nC

Taiwan Semiconductor

VALUE

100

90

100

9.3

HALOGEN

# **N-Channel Power MOSFET**

100V, 15A,  $90m\Omega$ 

#### FEATURES

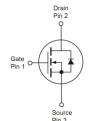
- 100% avalanche tested
- Low gate charge for fast switching
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

#### APPLICATION

- Networking
- Load Switching
- LED Lighting Control
- AC-DC Secondary Rectification







**KEY PERFORMANCE PARAMETERS** 

 $V_{GS} = 10V$ 

 $V_{GS} = 4.5V$ 

PARAMETER

V<sub>DS</sub>

Qg

R<sub>DS(on)</sub> (max)

Notes: Moisture sensitivity level: level 3. Per J-STD-020

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$	- I <sub>D</sub>	15	А
Continuous Drain Current (Note 1)	$T_{\rm C} = 100^{\circ}{\rm C}$		9.5	
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	60	А
Total Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>DTOT</sub>	50	W
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	18	mJ
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	6	А
Operating Junction and Storage Temperature Range		$T_J, T_STG$	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	2.5	°C/W	
Junction to Ambient Thermal Resistance	R <sub>⊖JA</sub>	62	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air.

# TSM900N10



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ELECTRICAL SPECIFICA	<b>TIONS</b> ( $T_A = 25^{\circ}C$ unles	s otherwise no	oted)	I	I	1
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV <sub>DSS</sub>	100			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.6	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
	$V_{GS} = 10V, I_{D} = 5A$	R <sub>DS(on)</sub>		72	90	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_{D} = 3A$			75	100	
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge		Qg		9.3		
Gate-Source Charge	$V_{DS} = 48V, I_D = 5A,$	Q <sub>gs</sub>		2.1		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_gd$		1.8		
Input Capacitance		C <sub>iss</sub>		1480		
Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$	C <sub>oss</sub>		480		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		35		
Gate Resistance	F = 1MHz, open drain	R <sub>g</sub>		1.3		Ω
Switching (Note 6)						•
Turn-On Delay Time		t <sub>d(on)</sub>		2.9		
Turn-On Rise Time	$V_{DD} = 30V,$ $R_{GEN} = 3.3\Omega,$ $I_D = 1A, V_{GS} = 10V,$	t <sub>r</sub>		9.5		
Turn-Off Delay Time		t <sub>d(off)</sub>		18.4		ns
Turn-Off Fall Time		t <sub>f</sub>		5.3		
Source-Drain Diode (Note 4)	1			•	•	
Forward On Voltage	$I_{\rm S} = 3.3$ A, $V_{\rm GS} = 0$ V	V <sub>SD</sub>			1	V
Continuous Drain-Source Diode		Is			15	Α
Pulse Drain-Source Diode	$V_{G}=V_{D}=0V$ , Force Current	I <sub>SM</sub>			60	Α

#### Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. L = 0.1mH,  $I_{AS}$  = 6A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25 $^{\circ}C$ 

4. Pulse test: PW  $\leq$  300µs, duty cycle  $\leq$  2%

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.



# **ORDERING INFORMATION (EXAMPLE)**

PART NO.	PACKAGE	PACKING
TSM900N10CH X0G	TO-251S (IPAK SL)	75pcs / Tube
TSM900N10CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

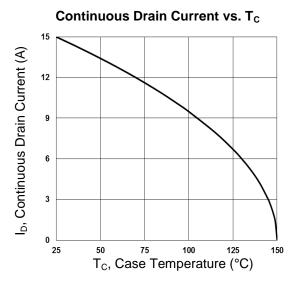
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

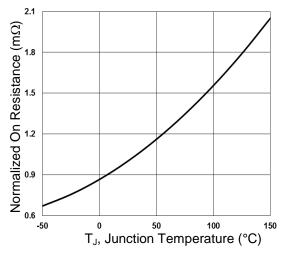


#### **CHARACTERISTICS CURVES**

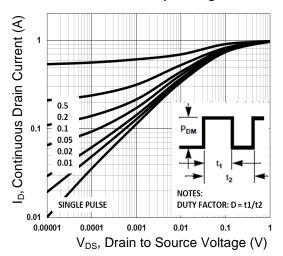
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 

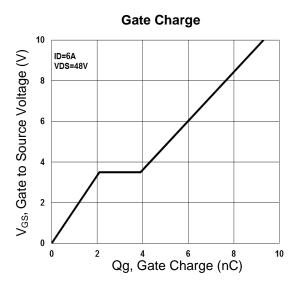


**On-Resistance vs. Junction Temperature** 

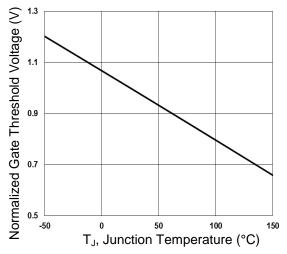


Maximum Safe Operating Area

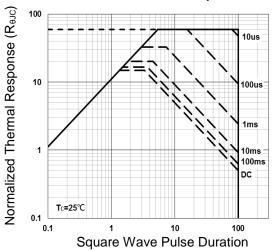




**Threshold Voltage vs. Junction Temperature** 

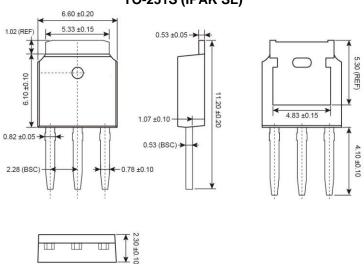


Normalized Thermal Transient Impedance Curve





## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### **MARKING DIAGRAM**

	$\square$	
	900N10 YML	
#		

Y = Year Code

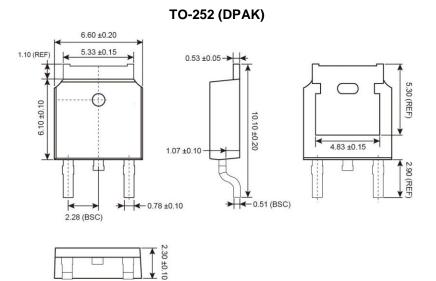
**M** = Month Code for Halogen Free Product

	<b>O</b> =Jan	P =Feb	<b>Q</b> =Mar	<b>R</b> =Apr
•	<b>S</b> =May	<b>T</b> =Jun	U =Jul	V =Aug
	W =Sep	X =Oct	Y =Nov	Z =Dec
L	= Lot Code (1-	~9, A~Z)		

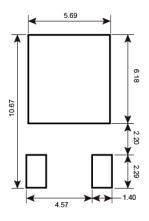




## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



### SUGGESTED PAD LAYOUT



#### **MARKING DIAGRAM**

	<ul><li>Y = Year Code</li><li>M = Month Code for Halogen Free Product</li></ul>
900N10 YML	O=JanP=FebQ=MarR=AprS=MayT=JunU=JulV=Aug
() U () #1U U	<b>W</b> =Sep <b>X</b> =Oct <b>Y</b> =Nov <b>Z</b> =Dec <b>L</b> = Lot Code (1~9, A~Z)



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